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(71) Applicant: **YANGTZE MEMORY TECHNOLOGIES CO., LTD.**, [CN/CN]; No. 88 Weilai 3rd Road, East Lake High-tech Development Zone, Wuhan, Hubei 430000 (CN).

(72) Inventors: **WANG, Di**; No. 88 Weilai 3rd Road, East Lake High-tech Development Zone, Wuhan, Hubei 430000 (CN). **GU, Yan**; No. 88 Weilai 3rd Road, East Lake High-tech Development Zone, Wuhan, Hubei 430000 (CN). **XIA, Zhiliang**; No. 88 Weilai 3rd Road, East Lake High-tech Development Zone, Wuhan, Hubei 430000 (CN). **ZHOU, Wenxi**; No. 88 Weilai 3rd Road, East Lake High-tech Development Zone, Wuhan, Hubei 430000 (CN). **HUO, ZongLiang**; No.

88 Weilai 3rd Road, East Lake High-tech Development Zone, Wuhan, Hubei 430000 (CN).

(74) Agent: **NTD UNIVATION INTELLECTUAL PROPERTY AGENCY LTD.**; 10th Floor, Tower C, Beijing Global Trade Center, 36 North Third Ring Road East, Dongcheng District, Beijing 100013 (CN).

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(54) Title: THREE-DIMENSIONAL MEMORY DEVICE WITH DIVIDED DRAIN SELECT GATE LINES AND METHOD FOR FORMING THE SAME

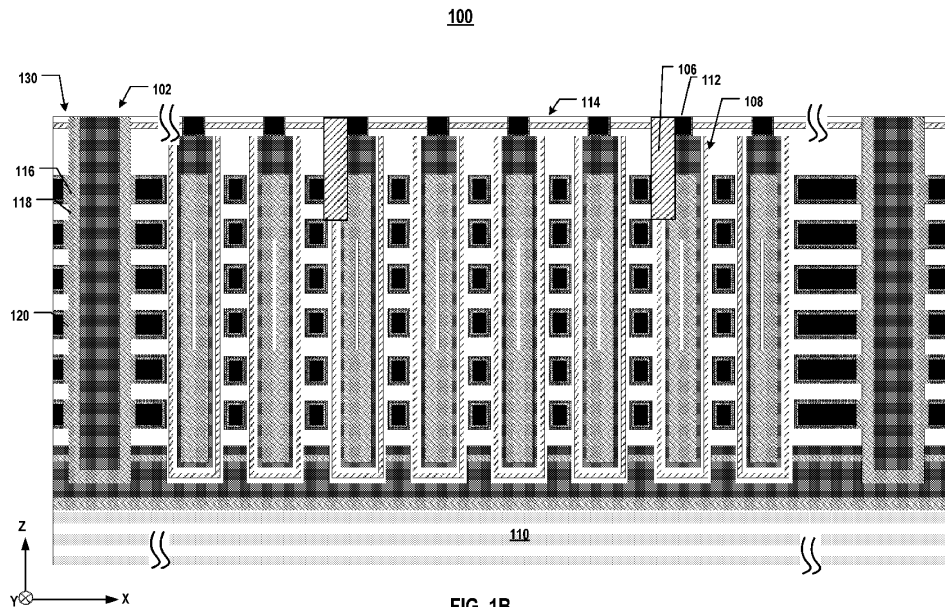


FIG. 1B

(57) Abstract: A memory device includes a stack structure over a substrate, a channel structure extending in the stack structure, and a dielectric layer over the channel structure. The dielectric layer includes a first material. The memory device may also include a drain-select gate (DSG) cut structure extending through the dielectric layer. The DSG cut structure includes a second material different from the first material.

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